

# Heterogeneous defect domains in h-WS<sub>2</sub>

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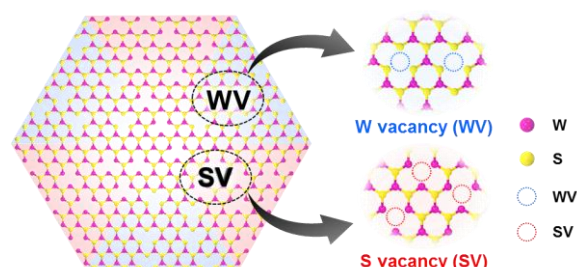
Although intricate defects are inevitably generated during the synthesis of transition metal dichalcogenides by chemical vapor deposition (CVD), the related discussions are mostly limited to chalcogen vacancies.<sup>[1-3]</sup> Here, we report the prevailing role of metal vacancies determining macroscopic material properties using a single-crystalline monolayer 2H-WS<sub>2</sub> grown by CVD. The hexagonal shape of the WS<sub>2</sub> flake is segmented into alternating triangular domains without forming explicit defective grain boundaries: sulfur-vacancy (SV)-rich and tungsten-vacancy (WV)-rich domains. The WV-rich domain with deep-trap states<sup>[4-6]</sup> revealed an electron-dedoping effect, and its electron mobility and photoluminescence were lower by one order of magnitude than those of the SV-rich domain with shallow-donor states.<sup>[7]</sup> The vacancy-induced strain and doping effects in such domains were investigated by analyzing spectral changes via Raman spectroscopy and the core-level shift via scanning photoelectron microscopy. Our work sheds light on tailoring macroscopic physical properties of two-dimensional materials via native defect engineering.

## References

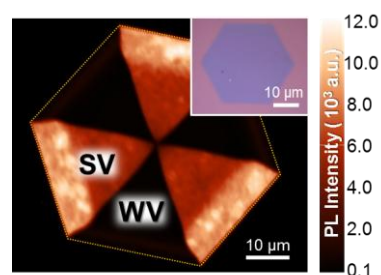
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## Figures



**Figure 1:** Schematic of heterogeneous defect domains in h-WS<sub>2</sub>



**Figure 2:** Photoluminescence intensity mapping image of h-WS<sub>2</sub>. Inset shows its optical image.